

**Intriguing Interfacial Characteristics of CS Contact to  $\text{MX}_2$   
( $\text{M}=\text{Mo}, \text{W}$ ;  $\text{X}=\text{S}, \text{Se}, \text{Te}$ ) and  $\text{MXY}$  ( $(\text{X}\neq\text{Y}) = \text{S}, \text{Se}, \text{Te}$ )  
Monolayers**

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## Supplementary Informations

Table SI: Lattice constant ( $a$  in Å), bond length (in Å), Work function ( $\phi$  in eV) and potential ( $\Delta V$  in eV) of CS-MX<sub>2</sub> (M=Mo, W; X=S, Se, Te) and CS-MXY ((X≠Y)=S,Se,Te) MS vdWH.

CS-MX <sub>2</sub>	CS-MoS <sub>2</sub>	CS-MoSe <sub>2</sub>	CS-MoTe <sub>2</sub>	CS-WS <sub>2</sub>	CS-WSe <sub>2</sub>	CS-WTe <sub>2</sub>
$\phi$	2.15	1.92	2.52	2.18	2.25	3.00
$\Delta V$	-9.88	-13.78	-0.53	-9.88	-12.88	-1.84
$m_h^*$	0.025	0.092	0.074	0.039	0.071	0.102
$m_e^*$	0.019	0.039	0.051	0.027	0.051	0.082

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CS-MXY(Model-I)	CS-MoSSe	CS-MoSTe	CS-MoSeTe	CS-WSSe	CS-WSTe	CS-WSeTe
$\phi$	2.15	2.96	2.46	1.96	2.19	2.25
$\Delta V$	-9.88	-9.63	-12.76	-10.14	-9.36	-11.68
$m_h^*$	0.058	0.087	0.064	0.052	0.086	0.074
$m_e^*$	0.024	0.050	0.038	0.029	0.047	0.061

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CS-MXY(Model-II)	CS-MoSSe	CS-MoSTe	CS-MoSeTe	CS-WSSe	CS-WSTe	CS-WSeTe
$\phi$	1.90	2.44	2.24	1.70	2.19	2.53
$\Delta V$	-12.48	-0.24	-1.12	-13.26	-0.88	-1.05
$m_h^*$	0.079	0.13	0.087	0.103	0.073	0.118
$m_e^*$	0.037	0.09	0.054	0.079	0.051	0.064

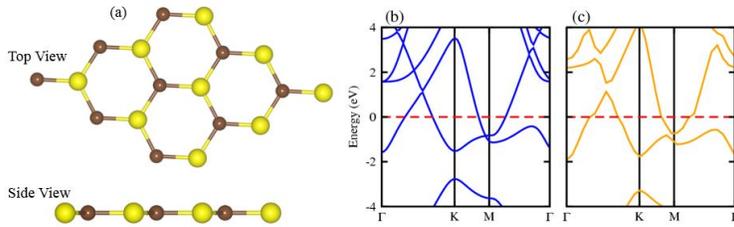


Figure S1. (a)Top and side view of the geometrical structure along with the band structure using (b)PBE, and (c)HSE06 functional for CS monolayer.

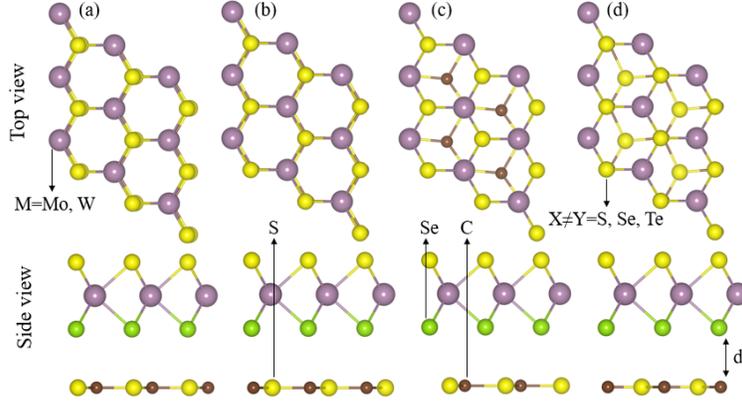


Figure S2. Possible stacking configurations of the ((a)-(d)) CS-MXY (M=Mo, W; X=S, Se, Te) MS vdWH in model-II, see text for details.

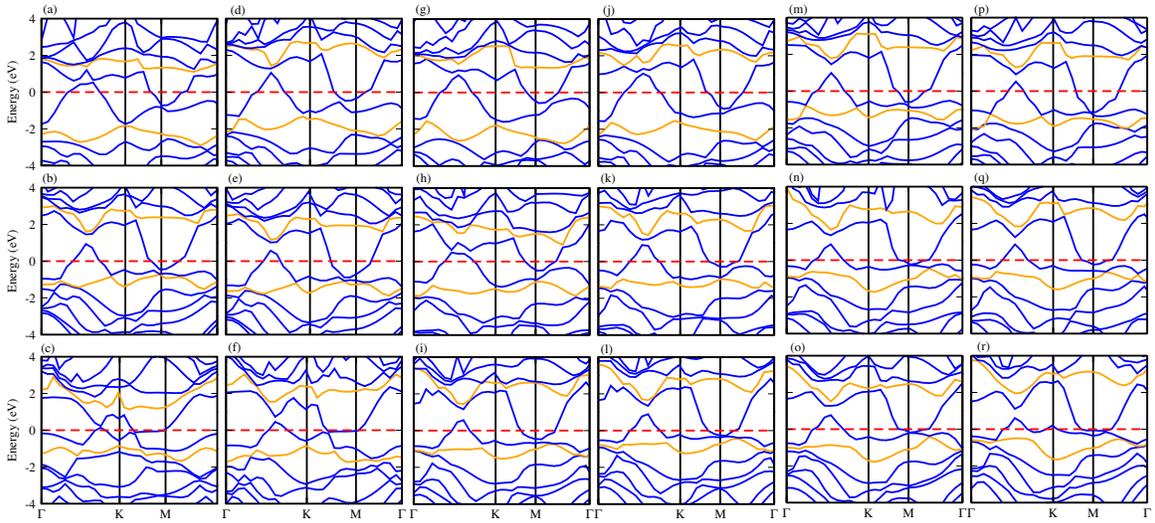


Figure S3. Band structures of (a) CS-MoS<sub>2</sub>, (b) CS-MoSe<sub>2</sub>, (c) CS-MoTe<sub>2</sub>, (d) CS-WS<sub>2</sub>, (e) CS-WSe<sub>2</sub>, (f) CS-WTe<sub>2</sub>, (g) CS-MoSSe, (h) CS-MoS<sub>2</sub>Te, (i) CS-MoSeTe, (j) CS-WSSe, (k) CS-WSTe, (l) CS-WSeTe, (m) CS-MoSeS, (n) CS-MoTeS, (o) CS-MoTeSe, (p) CS-WSeS, (q) CS-WTeS, (r) CS-WTeSe MS vdWH using HSE06 functionals.

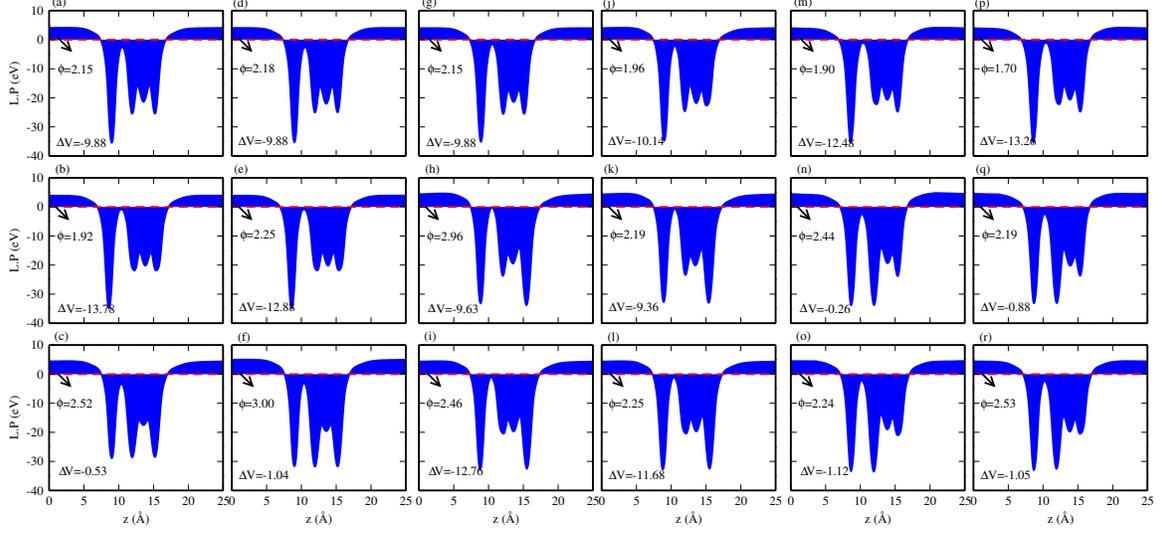


Figure S4. Average electrostatic potential of (a) CS-MoS<sub>2</sub>, (b)CS-MoSe<sub>2</sub>, (c)CS-MoTe<sub>2</sub>, (d) CS-WS<sub>2</sub>, (e) CS-WSe<sub>2</sub>, (f) CS-WTe<sub>2</sub>, (g)CS-MoSSe, (h)CS-MoSTe (i) CS-MoSeTe, (j) CS-WSSe, (k) CS-WSTe, (l) CS-WSeTe, (m) CS-MoSeS (n) CS-MoTeS (o) CS-MoTeSe (p) CS-WSeS, (q) CS-WTeS (r) CS-WTeSe MS vdWH using HSE06 functionals.

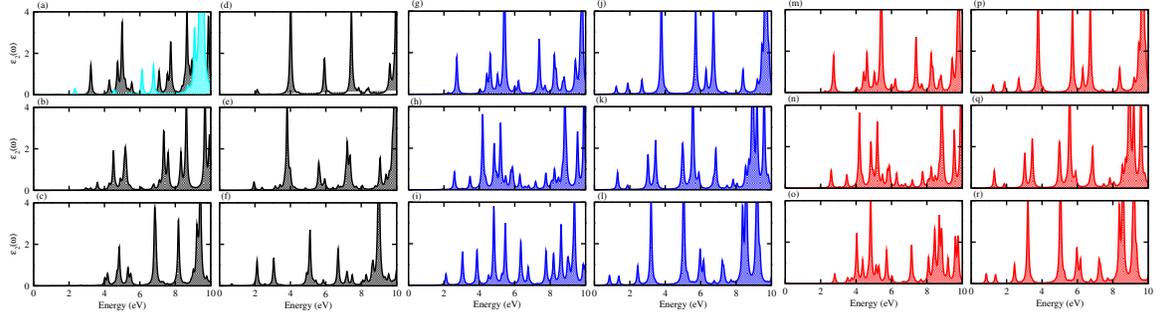


Figure S5.  $\epsilon_2(\omega)$  of (a) MoS<sub>2</sub> (CS), (b) MoSe<sub>2</sub>, (c) MoTe<sub>2</sub>, (d) WS<sub>2</sub>, (e) WSe<sub>2</sub>, (f) WTe<sub>2</sub>, (g) MoSSe, (h)MoSTe (i)MoSeTe, (j) WSSe, (k) WSTe, (l) WSeTe, (m) MoSeS (n) MoTeS (o) MoTeSe (p) WSeS, (q) WTeS (r) WTeSe monolayers.